Prof. Ohmi's Paper

January ─December, 1995

E529(C) T. Ohmi, Y. Okada, T. Yabune and K. Ohmi, "High Integrity Thin SiO_2 Free from Contamination and Micro-Roughness," 22nd Annual Conference on the Physics and Chemistry of Semiconductor Interfaces(PCSI-22), (1page), Invited, Old Town Scottsdale, Arizona, January 1995.

E530(C) Tadahiro Ohmi, "Advanced Sub-Half Micron Processing Based on Ultraclean Technology," Proceeding of the 12th Symposium on PLASMA PROCESSING, pp. 167-188, Sendai, Japan, January 1995.

E531 (F) Hiroshi Nohira, Kenji Saito, Kenichi Sakusabe, Koji Makihara, Mizuho Morita, Tadahiro Ohmi and Takeo Hattori, "Effect of Preoxide on the Structure of Thermal Oxide," Jpn. J. Appl. Phys., Vol. 34, Part. 1, No. 1, pp. 245-248, January 1995.

E532 (F) Hideo Kosaka, Tadashi Shibata, Hiroshi Ishii and Tadahiro Ohmi, "An Excellent Weight-Updating-Linearity EEPROM Synapse Memory Cell for Self-Learning Neuron-MOS Neural Networks," IEEE Trans. on Electron Devices, Vol. 42, No. 1, pp. 135-143, January 1995.

E533 (F) Tadahiro Ohmi, K. Matsumoto, K. Nakamura, K. Makihara, J. Takano and K. Yamamoto, "Influence of Silicon Wafer Surface Orientation on Very Thin Oxide Quality," J. Appl. Phys., Vol. 77, No. 3, pp. 1159-1164, January 1995.

E534(C) Koji Kotani, Tadashi Shibata, Makoto Imai and Tadahiro Ohmi, "Clocked-Neuron-MOS Logic Circuits Employing Auto-Threshold-Adjustment," Digest of Technical Papers, 1995 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pp. 320-321, 388, San Francisco, February 1995.

E535(C) Nobuhiro Miki, Matagoro Maeno, Toshiro Fukudome, Shin Sato, Koichi Yabe, Takashi Imaoka,Toru Okouchi, Ikuo Sindo and Tadahiro Ohmi, "Reformation of the Entire Waste Chemical Disposal System for the Semiconductor Manufacturing Wet Process Using Advanced Recovery Technology of Pure Fluoride and Phosphate," 1995 Semiconductor Pure Water and Chemicals Conference, Santa Clara, pp. 113-130, February 1995.

E536(C) Fumitomo Kunimoto, Masashi Nose and Tadahiro Ohmi, "The State-of-the-Art Membrane Filter for Wet Chemicals Recirculating Filtration," 1995 Semiconductor Pure Water and Chemicals Conference, Santa Clara, pp. 153-170, February 1995.

E537(C) Hirohisa Kikuyama, Jun Takano, Masayuki Miyashita, Tatsuhiko Yabune, Hiroto Izumi and Tadahiro Ohmi, "Optimization of Composition of Buffered Hydrogen Fluoride for ULSI Processing," 1995 Semiconductor Pure Water and Chemicals Conference, Santa Clara, pp. 237-259, February 1995.

E538(C) Masashi Nose, Senri Ojima, Kazuki Kubo and Tadahiro Ohmi, "Carbon Contamination Free Silicon Wafer Surface," 1995 Semiconductor Pure Water and Chemicals Conference, Santa Clara, pp. 260-275, February 1995.

E539 (F) Mauricio Massazumi Oka, Akira Nakada, Kazuo Tomita, Tadashi Shibata and Tadahiro Ohmi, "Reducing Reverse-Bias Current in 450^{0}C-Annealed $n^{+}p$ Junction by Hydrogen Radical Sintering," Jpn. J. Appl. Phys., Vol. 24, Part 1, No. 2B, pp. 796-799, February 1995.

E540 (F) Wataru Shindo, Masaki Hirayama and Tadahiro Ohmi, "Abrupt and Arbitrary Profile Formation in Silicon Using a Low-Kinetic-Energy Ion Bombardment Process," Jpn. J. Appl. Phys., Vol. 24, Part 1, No. 2B, pp. 800-803, February 1995.

E541 (F) Jinzo Watanabe, Yasuaki Kawai, Nobuhiro Konishi and Tadahiro Ohmi, "Ultra Low-Temperature Growth of High-Integrity Thin Gate Oxide Films by Low-Energy Ion-Assisted Oxidation," Jpn. J. Appl. Phys., Vol. 24, Part 1, No. 2B, pp. 900-902, February 1995.

E542 (F) Shuhei Kondo, Tadashi Shibata and Tadahiro Ohmi, "Superior Generalization Capability of Hardware-Learning Algorithm Developed for Self-Learning Neuron-MOS Neural Networks," Jpn. J. Appl. Phys., Vol. 24, Part 1, No. 2B, pp. 1066-1069, February 1995.

E543 (F) Hitoshi Morinaga, Takashi Futatsuki, Tadahiro Ohmi, Eiji Fuchita, Masaki Oda and Chikara Hayashi, "Behavior of Ultrafine Metallic Particles on Silicon Wafer Surface," Journal of Electrochemical Society, Vol. 142, No. 3, pp. 966-970, March 1995.

E544 (F) M. Itano, T. Kezuka, M. Ishii, T. Unemoto, M. Kubo and Tadahiro Ohmi, "Minimization of Particle Contamination during Wet Processing of Si Wafers," Journal of Electrochemical Society, Vol. 142, No. 3, pp. 971-978, March 1995.

E545(C) Tadahiro Ohmi, "Ultraclean Processing for Future ULSI," Technical Conference, SEMICON/Europa, Geneva, Switzerland, April 1995.

E546(C) Tadahiro Ohmi, "Evaluation of Industry-University Relationships," Abstracts of Presentations, First International Conference on Evaluation of Research, Technology and Development, (European Commission Directorate General XII Science, Research and Development), (1page), Thessaloniki, Greece, April 1995.

E547(C) Tadahiro Ohmi, "Semiconductor Manufacturing Technology in the Year 2000," 1995 Japanese Semiconductor Industry Conference, (Dataquest Japan K. K.), Tokyo Hilton Hotel, pp. 0-61, April 1995.

E548(C) Steven Verhaverbeke, Rochidi Messoussi, Hitoshi Morinaga and Tadahiro Ohmi, "Recent Advances in Wet Processing Technology and Science," Ultraclean Semiconductor Processing Technology and Surface Chemical Cleaning and Passivation, MRS Symposium Proceedings, Vol. 386, pp. 3-12, 1995.

E549(C) Yasuyuki Shirai, Seok-Kiu Lee, Shinji Miyoshi and Tadahiro Ohmi, "The Evaluation of Thermal Decomposition Characteristics of Active Specialty Gases on Various Metal Surfaces Using FT-IR Method," 1995 Proceedings, 41st Annual Technical Meeting, Institute of Environmental Sciences, Anaheim, California, pp. 17-21, April/May 1995.

E550(C) T. Kojima, S. Ojima, K. Kubo, T. Yabune and T. Ohmi, "Transportation Technology of Si Wafer without Accompanying Carbon Contamination," 1995 Proceedings, 41st Annual Technical Meeting, Institute of Environmental Sciences, Anaheim, California, pp. 178-184, April/May 1995.

E551(C) T. Suenaga, M. Nose, S. Ojima, K. Kubo and T. Ohmi, "Consideration for the Sustenance of Surface Cleanliness in Wafer Transportation," 1995 Proceedings, 41st Annual Technical Meeting, Institute of Environmental Sciences, Anaheim, California, pp. 185-190, April/May 1995.

E552(C) S. Ojima, K. Kubo, M. Nose and T. Ohmi, "Establishment of Complete Cleaning Technology for Hydrocarbon Contamination on Si Wafer Surface," 1995 Proceedings, 41st Annual Technical Meeting, Institute of Environmental Sciences, Anaheim, California, pp. 441-446, April/May 1995.

E553(C) H. Izumi, Y. Nakagawa, M. Nakamura and T. Ohmi, "Behavior of Adsorbed Moisture on Solid Surfaces," 1995 Proceedings, 41st Annual Technical Meeting, Institute of Environmental Sciences, Anaheim, California, pp. 549-556, April/May 1995.

E554 (P) T. Ohmi, Y. Okada, T.Yabune and K. Ohmi, "Highly Reliable Thin SiO_2 Film Formation Technology," Reliable of Metals in Electronics, Edited by Hazara S. Rathore, PV95-3, The Electrochemical Society, Pennington, NJ, pp. 44-53, 1995.

E555(C) K. Ino, K. Yamada, G. S. Jong and T. Ohmi, "Oxygen-Contamination-Free Ultra-Low-Resistance Silicided Contact Technology for High Performance Power Devices," Proceedings, 7th International Symposium on Power Semiconductor Devices & IC's (ISPSD'95), Yokohama, pp. 434-437, May 1995.

E556(C) T. Takewaki, H. Yamada, T. Shibata, T. Ohmi and T. Nitta, "Excellent Electron/Stress-Migration-Resistance Giant-Grain Copper Interconnect Technology for High-Performance Power Devices," Proceedings, 7th International Symposium on Power Semiconductor Devices & IC's (ISPSD'95), Yokohama, pp. 438-442, May 1995.

E557 (F) K. Tomita, T. Migita, S. Shimonishi, T. Shibata and T. Ohmi, "Eliminating Metal-Sputter Contamination in Ion Implanter for Low-Temperature-Annealed, Low-Reverse-Bias-Current Junctions," Journal of Electrochemical Society, Vol. 142, No. 5, pp. 1692-1698, May 1995.

E558(C) T. Takewaki, T. Ohmi and T. Nitta, "A Novel Self-Aligned Surface-Silicide Passivation Technology for Reliability Enhancement in Copper Interconnects," Digest of Technical Papers, 1995 Symposium on VLSI Technology, Kyoto, pp. 31-32, June 1995.

E559(C) Wataru Shindo and Tadahiro Ohmi, "Low-Energy Large-Mass Ion Bombardment Process for Low-Temperature High-Quality Silicon Epitaxy," Digest of Technical Papers, 1995 Symposium on VLSI Technology, Kyoto, pp. 93-94, June 1995.

E560(C) Tadahiro OHMI, "Integrating Intelligence on Silicon Electronic Systems -An Inter-University Cooperative Research Project for Innovative Process, Device, Circuit, and System Technologies," Digest of Technical Papers, 1995 Symposium on VLSI Circuits, Kyoto, pp. 1-4, Invited Paper, June 1995.

E561 (M) T. Ohmi, "Novel Surface Cleaning Technology," Semiconductor Fabtech(I.C.G.Publishing Ltd.), Issue No. 2, pp. 79-82, 1995.

E562 (F) Tadahiro Ohmi, "Very High Quality Thin Gate Oxide Formation Technology," Journal of Vacuum Science and Technology A, Vol. 13, No. 3, pp. 1665-1670, May/June 1995.

E563(C) Tadahiro OHMI, Yasuyuki SHIRAI, Masaki NARAZAKI, and Tsutomu KOJIMA, "Advanced Gas Technology for Semiconductor and Liquid Crystal Process in The 21st Century," OSK-Semiconductor Seminar(Osaka Sanso Kogyo K. K.), pp. 55-74, June 1995.

E564(C) O. Tatsumi, K. Ino, A. Ichikawa, N. Nakano, and T. Ohmi, "New Planarization Technique Using Ion-Assisted Low-Temperature Surface Reflow of BPSG Film," Digest of Papers, MicroProcess'95 (The 8th International MicroProcess Conference), Sendai, pp. 90-92, July 1995.

E565(C) A. Ichikawa, K. Nakano, T. Sanbei, and T Ohmi, "Extremely High Selective Etching of Silicon over Resist in Nitrogen-added Trichlorophosphorus Plasma," Digest of Papers, MicroProcess'95 (The 8th International MicroProcess Conference), Sendai, pp. 98-99, July 1995.

E566(C) Tadahiro OHMI, Koji KOTANI, and Hisayuki SHIMADA, "Prospects to X-Ray and EUV Lithography," Digest of Papers, XEL'95(1995 International Workshop on X-ray and Extreme Ultraviolet Lithography), Osaka, pp. M-1-1-1 - M-1-1-9, July 1995.

E567 (F) Tsutomu KOJIMA, Masakazu NAKANURA, Yasuyuki SHIRAI, Masaki NARAZAKI, and Tadahiro OHMI, "Silane Gas Interactions with Various Silicon Surface," Technical Report of IECE, SDM95-56, ICD95-65, pp. 21-27, July 1995.

E568 (F) Kazuhide INO, Iwao NATORI, Akihiko ICHIKAWA, Raymond N. VRTIS, and Tadahiro OHMI, "In Situ Chamber Self-Cleaning Technology using NF_3 Plasma," Technical Report of IECE, SDM95-75, ICD95-84, pp. 37-43, July 1995.

E569 (F) Tsutomu NAKAI, Tadashi SHIBATA, Takeo YAMASHITA, and Tadahiro OHMI, "A Neuron-MOS Data Sorting Circuit," Technical Report of IECE, SDM95-83, ICD95-92, pp. 87-92, July 1995.

E570 (F) M. Imai, K. Kotani, T. Shibata, and T. Ohmi, "Clocked Neuron-MOS Circuit Technology for Highly-Reliable Logic Operations," Technical Report of IECE, SDM95-84, ICD95-93, pp. 93-98, July 1995.

E571 (F) Senri OJIMA, Kazuki KUBO, Hiroto IZUMI, Masashi NOSE, Tadahiro OHMI, and Masayuki TODA, "Advanced Wet Cleaning of Wafers with Reduced Chemicals and DI Water Consumption," Technical Report of IECE, SDM95-86, ICD95-95, pp. 105-112, July 1995.

E572 (F) TADAHIRO OHMI, SHINJI MIYOSHI, YASUYUKI SHIRAI, TSUTOMU KOJIMA, and YASUMITSU MIZUGUCHI, "Metal Fume-Free Welding Technology for Advanced Semiconductor Grade Gas Delivery System," Journal of Electrochemical Society, Vol. 142, No. 7, pp. 2362-2372, July 1995.

E573 (F) Tadashi Shibata, Hideo Kosaka, Hiroshi Ishii, and Tadahiro Ohmi, "A Neuron-MOS Neural Network Using Self-Learning-Compatible Synapse Circuits," IEEE Journal of Solid-State Circuits, Vol. 30, No. 8, pp. 913-922, August 1995.

E574(C) Tadahiro OHMI and Tadashi SHIBATA, "Four-Terminal Device Electronics for Intelligent Silicon Integrated System," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 1-3, Invited, August 1995.

E575(C) K. OHMI, T. Iwamoto, T. Yabune, T.Miyake, and T. Ohmi, "Formation Process of Highly Reliable Ultra-Thin Gate Oxide," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 258-260, August 1995.

E576(C) Akira NAKADA, Mauricio Massazumi OKA, Yukio TAMAI, Tadashi SHIBATA, Herzl AHARONI, and Tadahiro OHMI, "Effect of Substrate Boron Concentration on the Integrity of 450□C-Annealed Ion-Implanted Junctions," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 366-368, August 1995.

E577(C) Mikihiro KIMURA and Tadahiro OHMI, "Time-Dependent Dielectric Degradation (TDDD) Influenced by Ultraclean Oxidation Process," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 461-463, August 1995.

E578(C) H. Izumi, M. Nose, S. Ojima, K. Kubo, and T. Ohmi, "The Cleaning of Particle and Metallic Impurity on Si Wafer Surface by Fluorine Etchant," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 620-622, August 1995.

E579(C) Kazuhide INO and Tadahiro OHMI, "Modeling and Analysis of RF Plasma Using Electrical Equivalent Circuit," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 644-646, August 1995.

E580(C) Yashuyuki Shirai, Masakazu Nakamura, and Tadahiro Ohmi, "Specialty Gas Interactions with Various Silicon Surfaces," Extended Abstract, 1995 International Conference on Solid State Devices and Materials, Osaka, pp. 929-931, August 1995.

E581(C) Tadahiro OHMI and Tadashi SHIBATA, "Intelligence Implementation on Silicon Based on Four-Terminal Device Electronics," Proceedings, 20th International Conference on Microelectronics (MIEL'95), Vol. 1, pp. 11-18, Invited Keynote Paper, Nis, Serbia, September 1995.

E582(C) Tadahiro Ohmi, "Low Cost Production by Simplified Processing," International Symposium on Semiconductor Manufacturing, Proceedings ISSM '95, pp. 277-282, Invited Paper, Austin, Texas, September 1995.

E583(C) Masaki Hirayama, Kazuhide Ino, and Tadahiro Ohmi, "Analysis of RF Plasma Using Electrical Equivalent Circuit," International Symposium on Semiconductor Manufacturing, Proceedings ISSM '95, pp. 283-286, Austin, Texas, September 1995.

E584(C) T. Shibata, K. Ino, N. Konishi, T. Ohmi, C. Urano, and H. Enosawa, "Through-UHV-Pump Impurity Back Diffusion Under Large Gas Flow and Its Minimization," International Symposium on Semiconductor Manufacturing, Proceedings ISSM '95, (4 pages), Austin, Texas, September 1995.

E585 (F) T. Takewaki, H. Yamada, T. Shibata, T. Ohmi, and T. Nitta, "Formation of Giant-Grain Copper Interconnects by a Low-Energy Ion Bombardment Process for High-Speed ULSIs," Journal of Materials Chemistry and Physics, Vol. 41, pp. 182-191, 1995.

E586(C) H. Shimada, T. Ushiki, Y. Hirano, and T. Ohmi, "Tantalum-Gate SOI MOSFET's Featuring Excellent Threshold Voltage Control in Low-Power Applications," Proceedings, 1995 IEEE International SOI Conference, pp. 96-97, Tucson, Arizona, October 1995.

E587(C) H. Shimada and T. Ohmi, "Minimum Parasitic Resistance for Ultra-Thin SOI MOSFET with High-Permitivity Gate Insulator Performed by Lateral Contact Structure," Proceedings, 1995 IEEE International SOI Conference, pp. 98-99, Tucson, Arizona, October 1995.

E588-1(C) T. Ohmi, "Proposal of Advanced Wet Cleaning of Silicon Surface," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 429, pp. 680-681, Invited, October 1995.

E588-2 (P) Tadahiro Ohmi, "Proposal of Advanced Wet Cleaning of Silicon Surface," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 1-12, 1996.

E589(C) H. Izumi, M. Nose, S. Ojima, K. Kubo, and T. Ohmi, "Removal of Particle and Metallic Impurity on Si Wafer Surface by Fluorine Etchant," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 442, pp. 704-705, October 1995.

E590-1(C) M. TODA, M. KATO, K. KUBO, S. OJIMA, and T. OHMI, "Radical Activation of DI Water and Cleaning Solution by Megasonic," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 444, pp. 708-709, October 1995.

E590-2 (P) Masayuki TODA, Masayuki KATO, Kazuki KUBO, Senri OJIMA, and Tadahiro OHMI, "Radical Activation of DI Water and Cleaning Solution by Megasonic," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 99-106, 1996.

E591-1(C) K. KUBO, S. OJIMA M. TODA, and T. OHMI, "Study on Megasonic in Advanced Wet Cleaning Process," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 445, pp. 710-711, October 1995.

E591-2 (P) K. Kubo, S. Ojima, M. Toda, and T. Ohmi, "Study on Megasonic in Advanced Wet Cleaning Process," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 107-114, 1996.

E592-1(C) Yasuyuki Shirai, Masakazu Nakamura, and Tadahiro Ohmi, "Specialty Gas Interactions with Ultraclean Silicon Surfaces," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 464, pp. 734-735, October 1995.

E592-2 (P) Yasuyuki Shirai, Masakazu Nakamura, and Tadahiro Ohmi, "Specialty Gas Interactions with Ultraclean Silicon Surfaces," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 251-256, 1996.

E593-1(C) Hitoshi Morinaga and Tadahiro Ohmi, "Electrochemical Deposition and Removal of Metallic Impurities on Si Surfaces," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 465, pp. 736-737, Invited, October 1995.

E593-2 (P) Hitoshi Morinaga and Tadahiro Ohmi, "Electrochemical Deposition and Removal of Metallic Impurities on Si Surfaces," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 257-268, 1996.

E594(C) M. Nose, H. Izumi, S. Ojima, K. Kubo, and T. Ohmi, "The Deposition Mechanism of Metal onto Si Surface in Cleaning Solution," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 469, pp. 743-744, October 1995.

E595-1(C) M. Meuris, H. Izumi, T. Ohmi, and M. M. Heyns, "Determination of the H-Passivation Build-Up Time in DHF-Treatments," Extended Abstracts, 188th Electrochemical Society Meeting, Chicago, Illinois, Abstract No. 492, pp. 782-783, October 1995.

E595-2 (P) M. Meuris, H. Izumi, K. Kubo, S. Ojima, T. Ohmi, and M. M. Heyns, "Determination of the H-Passivation Build-Up Time in DHF-Treatments," Cleaning Technology in Semiconductor Device Manufacturing, Edited by Richard E. Novak and Jerzy Ruzyllo, PV95-20, The Electrochemical Society, Pennington, NJ, pp. 444-448, 1996.

E596(P) Tadahiro Ohmi, "Advanced Plasma Processing with Accurately Controlled Ion Flux and Energy," Proceedings, the 3rd IUMRS International Conference in Asia(IUMRS-ICA-'95), Fabrication and Characterization of Advanced Materials, Edited by S. W. Kim and S. J. Park, pp. 3-9, Plenary Lecture, Seoul, Korea, October 1995.

E597(M) TADAHIRO OHMI, "High-Quality, High-Reliability, Low-Cost, Ultraclean Gas Distribution System," Semiconductor Fabtech, Global Issues & New Developments in Semiconductor Manufacturing, (I. C. G. Publishing Ltd.), Issue No. 3, pp. 153-162, 1995.

E598(C) Tadahiro Ohmi, "Future Manufacturing Technology in the year 2000," Proceedings of SPIE, Microelectronic Device and Multilevel Interconnection Technology, Vol.2636, pp. 16-22, Invited, Austin, Texas, October 1995.

E599(M) Tadahiro Ohmi, "Ultra-Clean Processing for ULSI," Microelectronics Journal, Vol.26, pp. 595-619, (1995 Elsevier Science Ltd.)

E600(M) Tadahiro Ohmi, "-Gas Tubing System- Corrosion-Free Cr_2O_3 Passivated Gas Tubing System for Specialty Gases," CLEANROOMS(in collaboration with Solid State Technology), Gas Handling and Delivery, pp. S18-S22, October 1995.

E601(P) Tadashi Shibata and Tadahiro Ohmi, "Neurontransistor:- A Neuron-Like High-Functionality Transistor Implementing Intelligence on Silicon," Proceedings, VLSI Signal Processing VIII, Edited by Takano Nishitani and Keshab K. Parhi, (Published under the sponsorship of the IEEE Signal Processing Society, pp. 28-37, October 1995.Invited

E602(W) Yasuhiko Kasama, Tadahiro Ohmi, Koichi Fukuda, Hirobumi Fukui, Chisato Iwasaki, Shoich Ono, "Improvemant of PECVD-SiNx for TFT Gate Insulator by Controlling Ion Bomberdment Energy," the 6th Microelectronics Conference Proceeding, pp.179-186, November 1995.

E603(W) Fumitomo Kunimoto and Tadahiro Ohmi, "Rapid Metal Removing by Spin Clearning Process," the 6th Microelectronics Conference Proceeding, pp.189-198, November 1995.

E604(W) K. Kubo, S. Ojima, Y. Sakata, M. Toda, M. Kato, and T. Ohmi, "Character Change of Ultrapure Water with Megasonic in New Wet Cleaning Process", the 6th Microelectronics Conference proceeding, pp.227-233, November 1995.

E605(C) F. Kunimoto, T. Ohmi, and M. Toda, "Characterization of Radical Activated Wafer Spin Cleaning Process," Abstracts, Materials Research Society 1995 Fall Meeting, AA4. 2, pp. 662, Boston, November-December 1995.

E606(C) Takashi Imaoka, Ken-ichi Mitsumori, Masayuki Toda, and Tadahiro Ohmi, "Improved Wet Cleaning Process Technology Using Electrolytic Ionized Water for Advanced TFT-LCD Manufacturing," Abstracts, Materials Research Society 1995 Fall Meeting, AA4. 3, pp. 662, Boston, November-December 1995.

E607-1(C) Yasuhiko Kasama, Tadahiro Ohmi, Koichi Fukuda, Hirobumi Fukui, Chisato Iwasaki, and Shoichi Ono, "Improvement of PECVD-SiNx for TFT Gate Insulator by Controlling Ion Bombardment Energy," Abstracts, Materials Research Society 1995 Fall Meeting, BB7. 9, pp. 674, Boston, November-December 1995.

E607-2(C) Yasuhiko Kasama, Tadahiro Ohmi, Koichi Fukuda, Hirobumi Fukui, Chisato Iwasaki, and Shoichi Ono, "Improvement of PECVD-SiNx for TFT Gate Insulator by Controlling Ion Bombardment Energy," Materials Research Society Symposium Proceedings, Vol. 415, pp. 57-64, 1996.

E608(C) T. Takewaki, R. Kaihara, T. Ohmi, and T. Nitta, "Excellent Electro/Stress-Migration-Resistance Surface-Silicide Passivated Giant-Grain Cu-Mg Alloy Interconnect Technology for Giga Scale Integration (GSI)," Technical Digest, International Electron Devices Meeting 1995, Washington, DC, pp. 253-256, December 1995.

E609(C) Hisayuki SHIMADA, Yuichi HIRANO, Takeo USHIKI, and Tadahiro OHMI, "Threshold Voltage Adjustment in SOI MOSFET's by Employing Tantalum for Gate Material," Technical Digest, International Electron Devices Meeting 1995, Washington, DC, pp. 881-884, December 1995.